

SPRAGUE-GOODMAN ELECTRONICS, INC.

HIGH Q ABRUPT TUNING VARACTOR DIODES

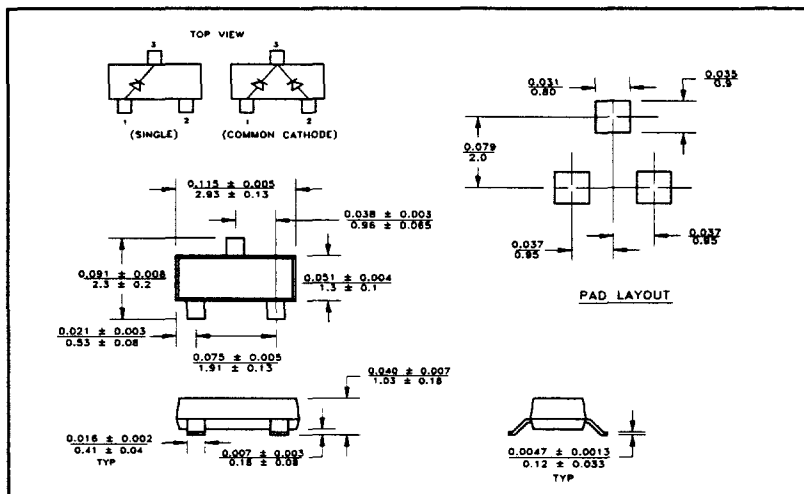
FEATURES

- Mesa Epitaxial Silicon Construction
- Silicon Dioxide Passivated
- Economy Price
- Mil grade Performance
- High Q
- Available in Common Cathode Style
- Available in Chip Form (add suffix -000)

SPECIFICATIONS

Reverse breakdown voltage (at 10 μ A DC) at 25°C: 30 V min
Maximum reverse leakage current (at -25 V) at 25°C: 0.05 μ A DC
Device dissipation (at 25°C): 250 mW (derated linearly to zero at +125°C)
Operating Junction temperature: -55°C to +125°C
Storage temperature: -55°C to +125°C

MODEL NUMBER		C_T (pF) at -4 V ($\pm 10\%$)	CAPACITANCE RATIO C_T at 0 V / C_T at -30 V min	Q min @ -4 V (50 MHz)
SINGLE	COMMON CATHODE			
GVD1202-001	GVD1202-004	1.2	3.4	3200
GVD1203-001	GVD1203-004	1.5	3.5	3000
GVD1204-001	GVD1204-004	1.8	3.5	3000
GVD1205-001	GVD1205-004	2.2	3.7	3000
GVD1206-001	GVD1206-004	2.7	3.7	2500
GVD1207-001	GVD1207-004	3.3	3.8	2500
GVD1208-001	GVD1208-004	3.9	3.9	2500
GVD1209-001	GVD1209-004	4.7	3.9	2000
GVD1210-001	GVD1210-004	5.6	4.0	2000
GVD1211-001	GVD1211-004	6.8	4.0	2000
GVD1212-001	GVD1212-004	8.2	4.0	2000
GVD1213-001	GVD1213-004	10.0	4.1	1800
GVD1214-001	GVD1214-004	12.0	4.1	1600
GVD1215-001	GVD1215-004	15.0	4.2	1250
GVD1216-001	GVD1216-004	18.0	4.2	1000
GVD1217-001	GVD1217-004	22.0	4.2	850



SOT-23 PACKAGE - consult factory for additional package configurations.

SPGOD00016